



PROTON-ELECTROTEX RUSSIA

High power cycling capability
Low on-state and switching losses
Optimized for line frequency rectifiers
Designed for traction and industrial applications

Rectifier Diode Type D143-1000-18

Average forward current				I_{FAV}	1000 A			
Repetitive peak reverse voltage				V_{RRM}	1000...1800 V			
V_{RRM} , V	1000	1100	1200	1300	1400	1500	1600	1800
Voltage code	10	11	12	13	14	15	16	18
T_j , °C	-60...+190							

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{FAV}	Maximum allowable average forward current	A	1000 1797	T _c =151 °C; Double side cooled; T _c =100 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FRMS}	RMS forward current	A	1570	T _c =151 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FSM}	Surge forward current	kA	20.0 24.0	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V
			21.0 25.0	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V
I ² t	Safety factor	A ² s·10 ³	2000 2800	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V
			1800 2500	T _j =T _{j max} T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V
BLOCKING					
V _{RRM}	Repetitive peak reverse voltages	V	1000...1800	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; 50 Hz	
V _{RSM}	Non-repetitive peak reverse voltages	V	1100...1900	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; single pulse	
V _R	Reverse continuous voltages	V	0.6·V _{RRM}	T _j =T _{j max} ;	
THERMAL					
T _{stg}	Storage temperature	°C	−60...+50		
T _j	Operating junction temperature	°C	−60...+190		
MECHANICAL					
F	Mounting force	kN	14.0...16.0		
a	Acceleration	m/s ²	50	Device clamped	

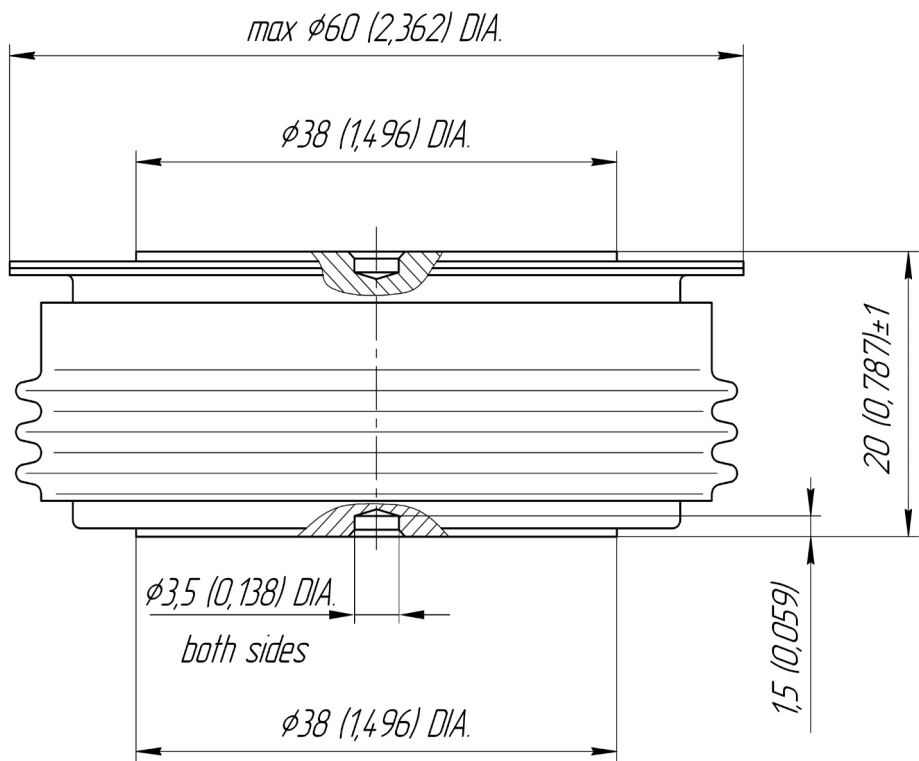
CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V_{FM}	Peak forward voltage, max	V	1.55	$T_j=25\text{ }^{\circ}\text{C}; I_{FM}=3140\text{ A}$
$V_{F(TO)}$	Forward threshold voltage, max	V	0.850	$T_j=T_{j\text{ max}};$
r_T	Forward slope resistance, max	$m\Omega$	0.228	$0.5\pi I_{FAV} < I_T < 1.5\pi I_{FAV}$
BLOCKING				
I_{RRM}	Repetitive peak reverse current, max	mA	70	$T_j=T_{j\text{ max}};$ $V_R=V_{RRM}$
SWITCHING				
Q_r	Recovered charge, max	μC	2340	$T_j=T_{j\text{ max}}; I_{TM}=1000\text{ A};$
t_{rr}	Reverse recovery time, max	μs	29	$di_R/dt=-10\text{ A}/\mu\text{s};$
I_{rr}	Reverse recovery current, max	A	161	$V_R=100\text{ V}$
THERMAL				
R_{thjc}	Thermal resistance, junction to case, max	$^{\circ}\text{C}/\text{W}$	0.027	Double side cooled
R_{thjc-A}			0.059	Anode side cooled
R_{thjc-K}			0.049	Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	$^{\circ}\text{C}/\text{W}$	0.006	Direct current
MECHANICAL				
m	Weight, max	g	250	
D_s	Surface creepage distance	mm (inch)	23.69 (0.933)	
D_a	Air strike distance	mm (inch)	19.10 (0.752)	

PART NUMBERING GUIDE

D	143	1000	18	N
1	2	3	4	5

1. D — Rectifier Diode
2. Design version
3. Average forward current, A
4. Voltage code
5. Ambient conditions: N – normal; T – tropical



All dimensions in millimeters (inches)

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In the interest of product improvement, Proton-Electrotex reserves the right to change data sheet without notice.

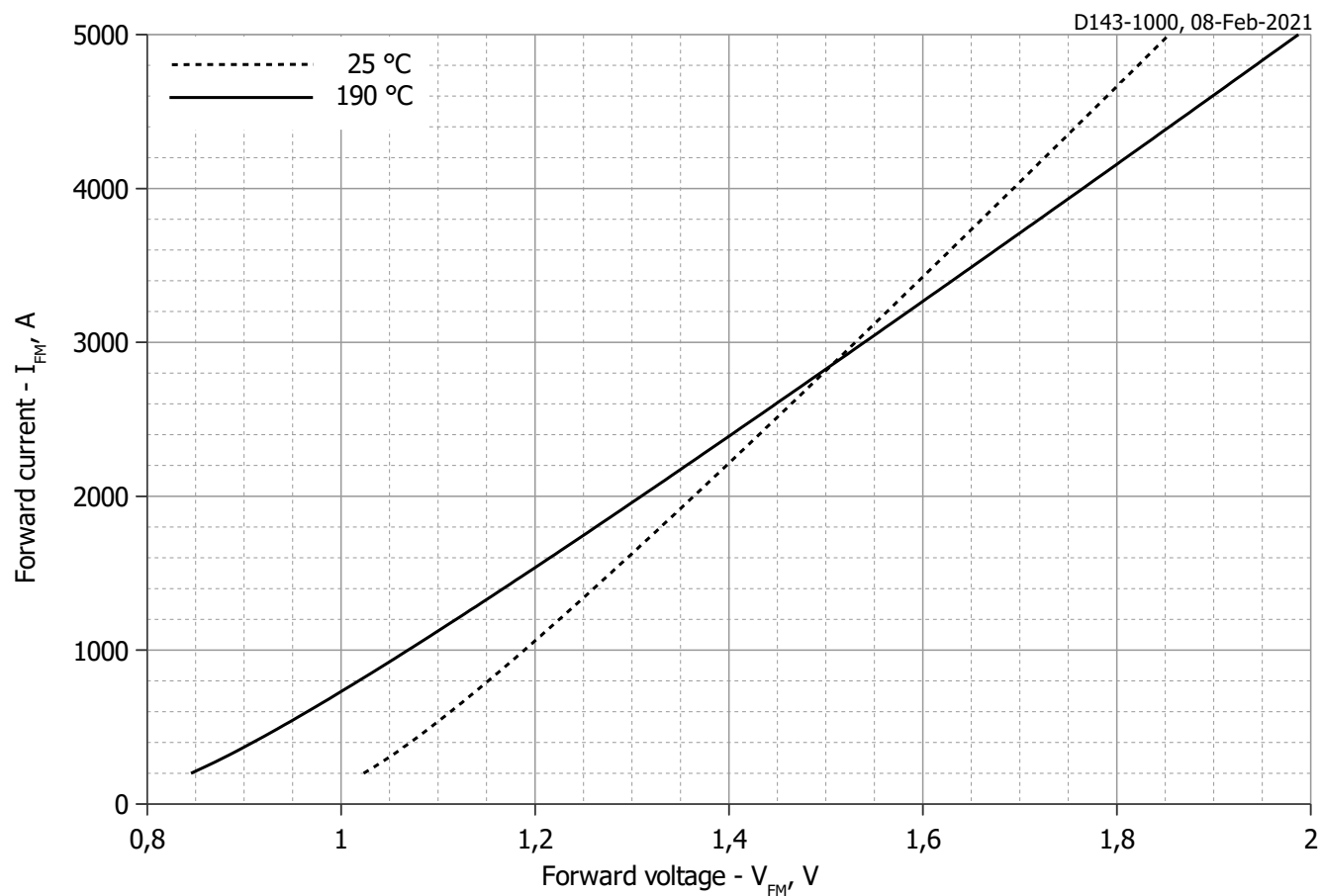


Fig 1 – Forward characteristics of Limit device

Analytical function for Forward characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j \max}$
A	0.88600330	0.68416775
B	0.00014906	0.00020532
C	0.01748542	0.01797983
D	0.00104422	0.00174547

Forward characteristic model (see Fig. 1).

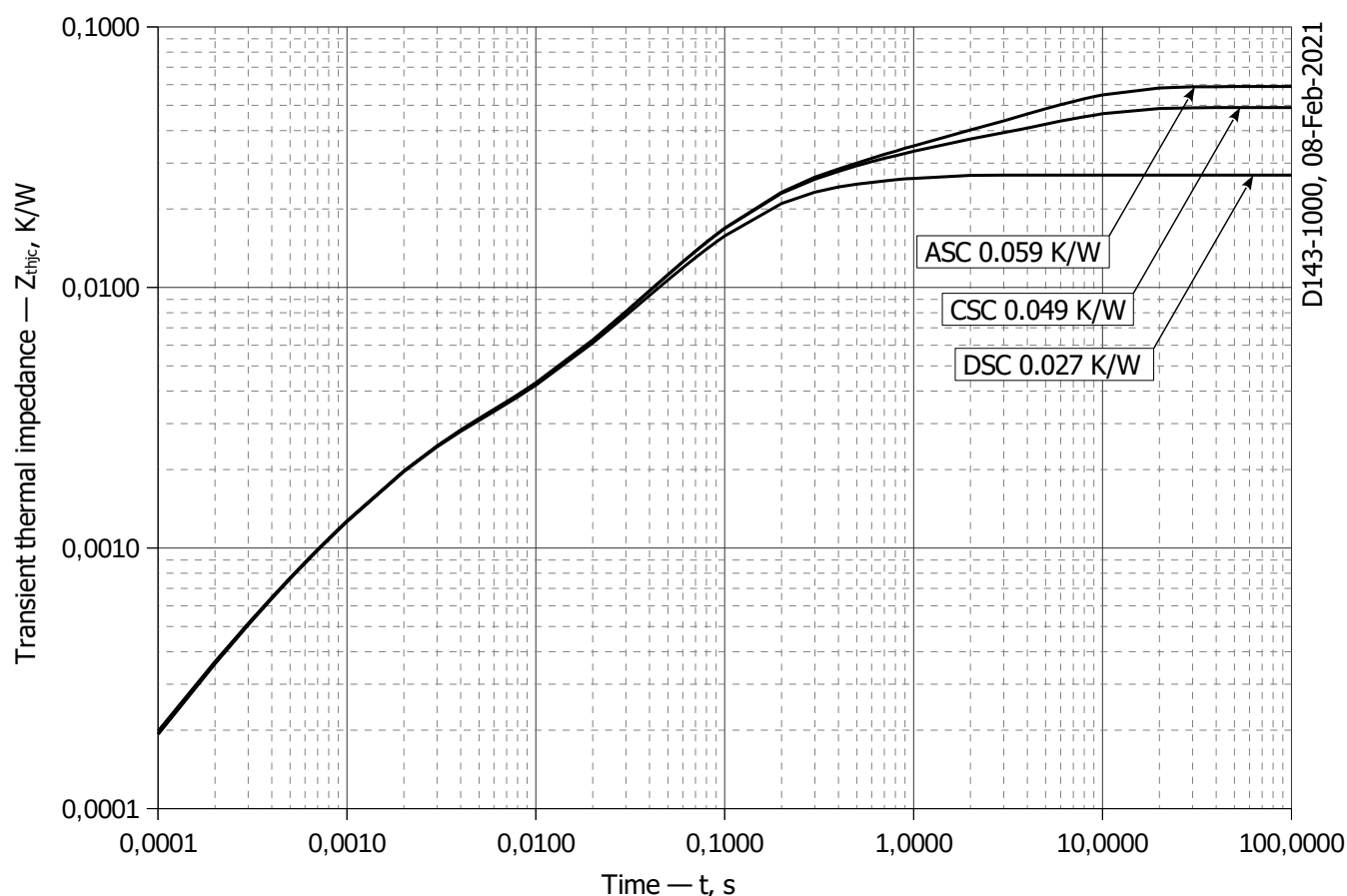


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i , K/W	0.00000562	0.00531	0.01922	0.0004148	0.0019	0.000152
τ_i , s	7.79	0.5094	0.09719	0.01725	0.0016	0.0002257

DC Cathode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.017	0.001472	0.01786	0.00193	0.000193	0.0105
τ_i , s	5.328	0.1832	0.09031	0.001714	0.0002598	0.525

DC Anode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.0267	0.008681	0.01867	0.00196	0.000179	0.00277
τ_i , s	5.351	0.4584	0.09325	0.001734	0.0002174	0.9059

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

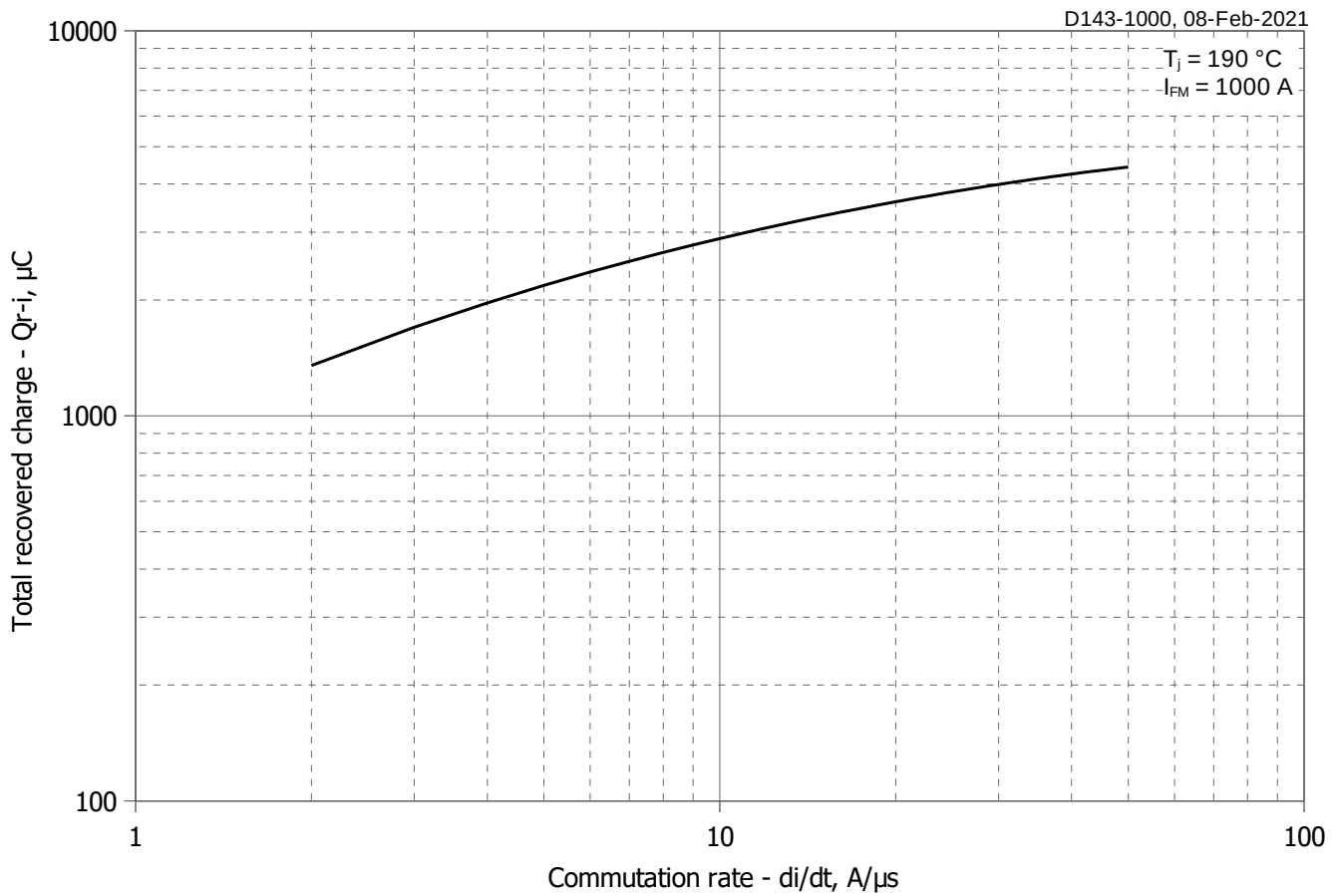


Fig 3 - Total recovered charge Q_{r-i} (integral) vs. commutation rate di_R/dt

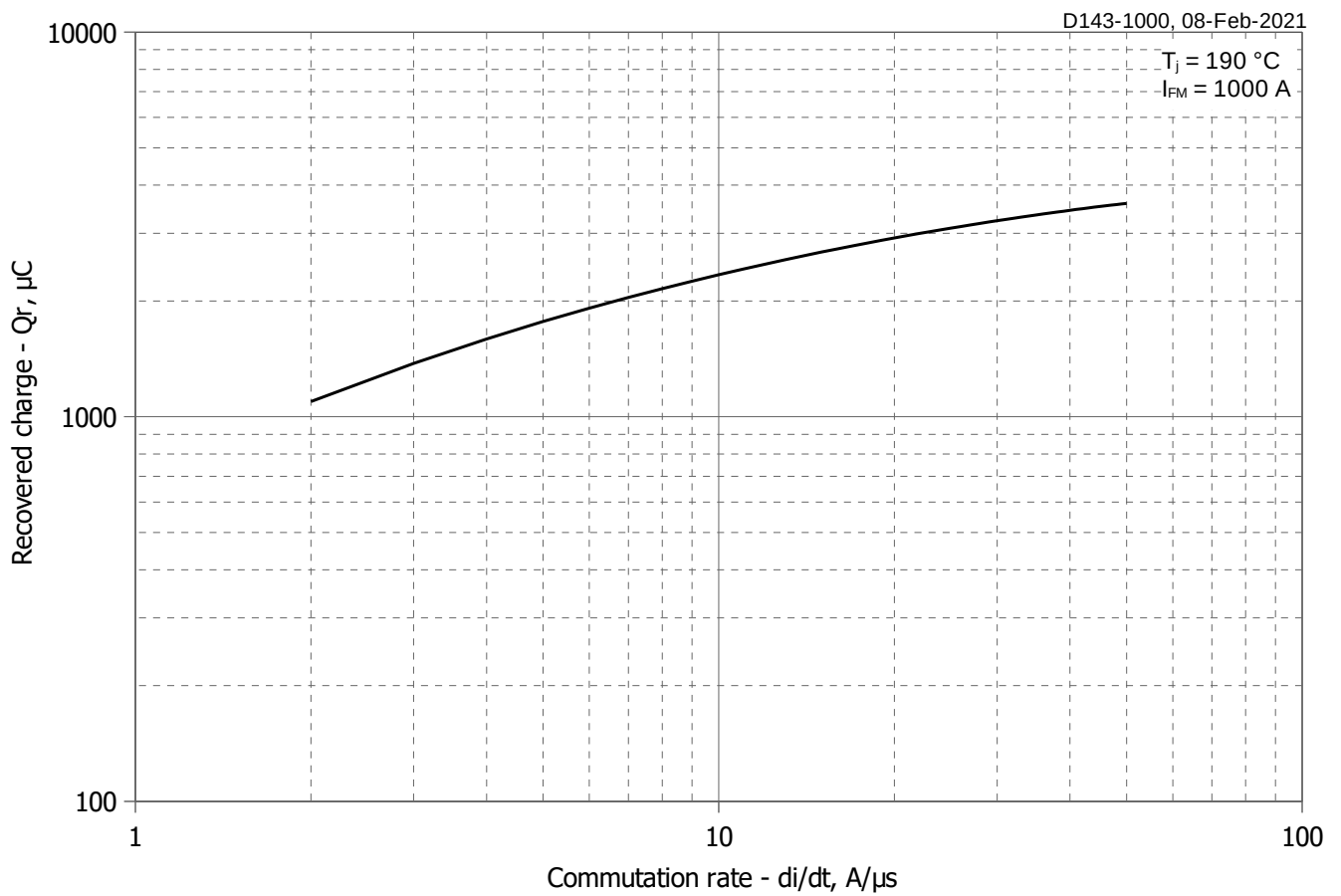


Fig 4 - Maximum recovered charge Q_r vs. commutation rate di_R/dt (25% chord)

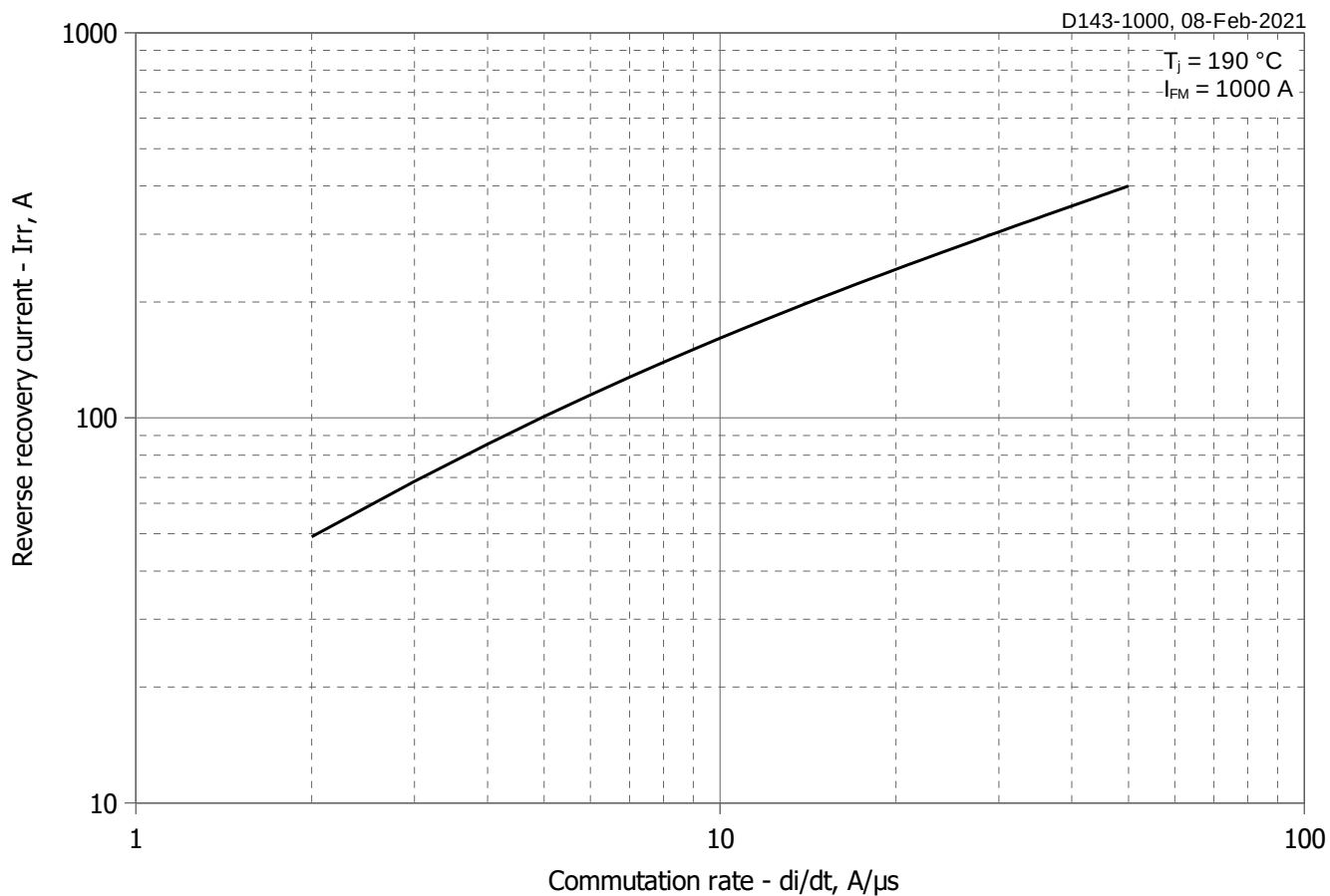


Fig 5 - Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

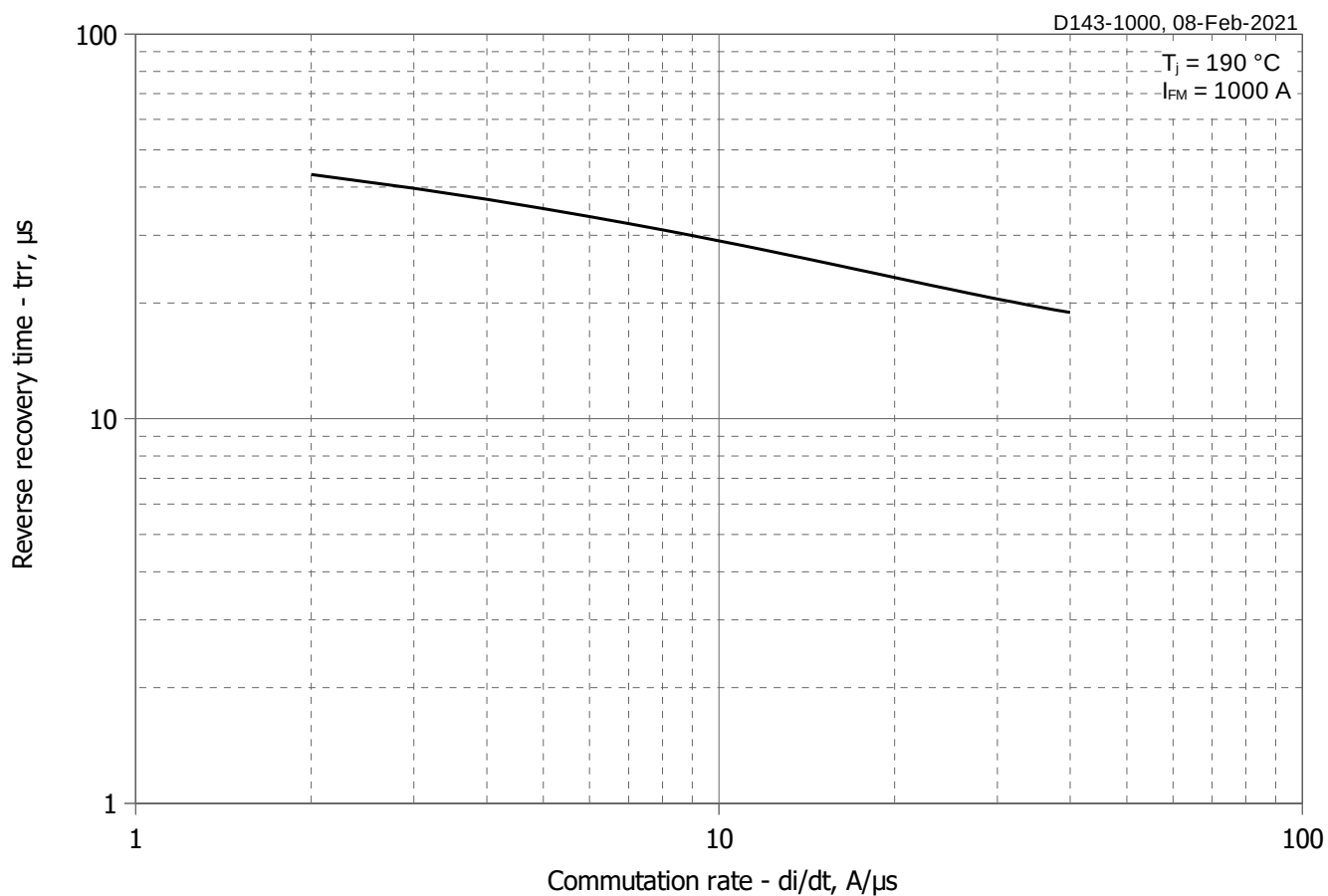


Fig 6 - Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

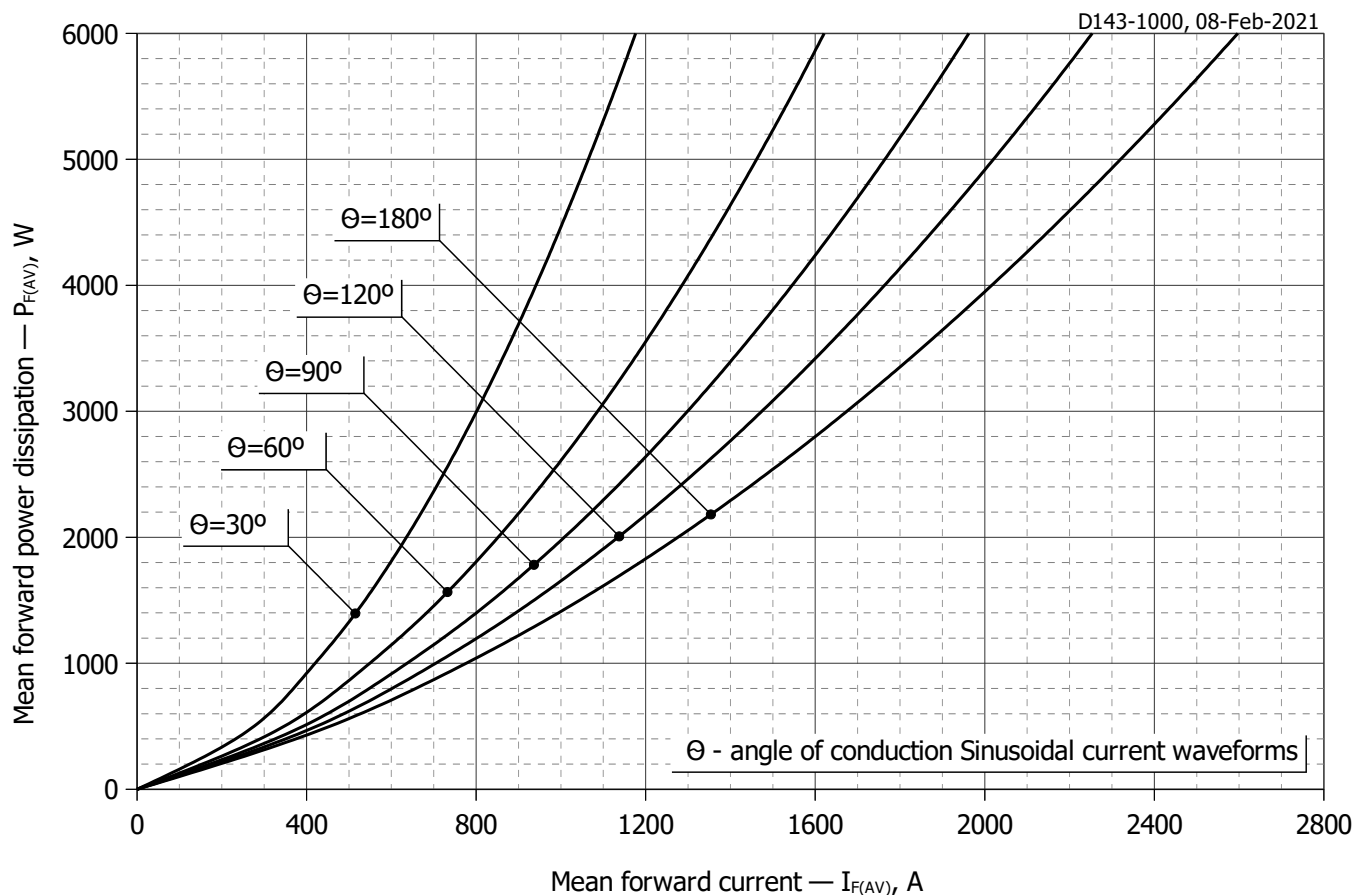


Fig. 7 - Mean forward power dissipation P_{FAV} vs. mean forward current I_{FAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

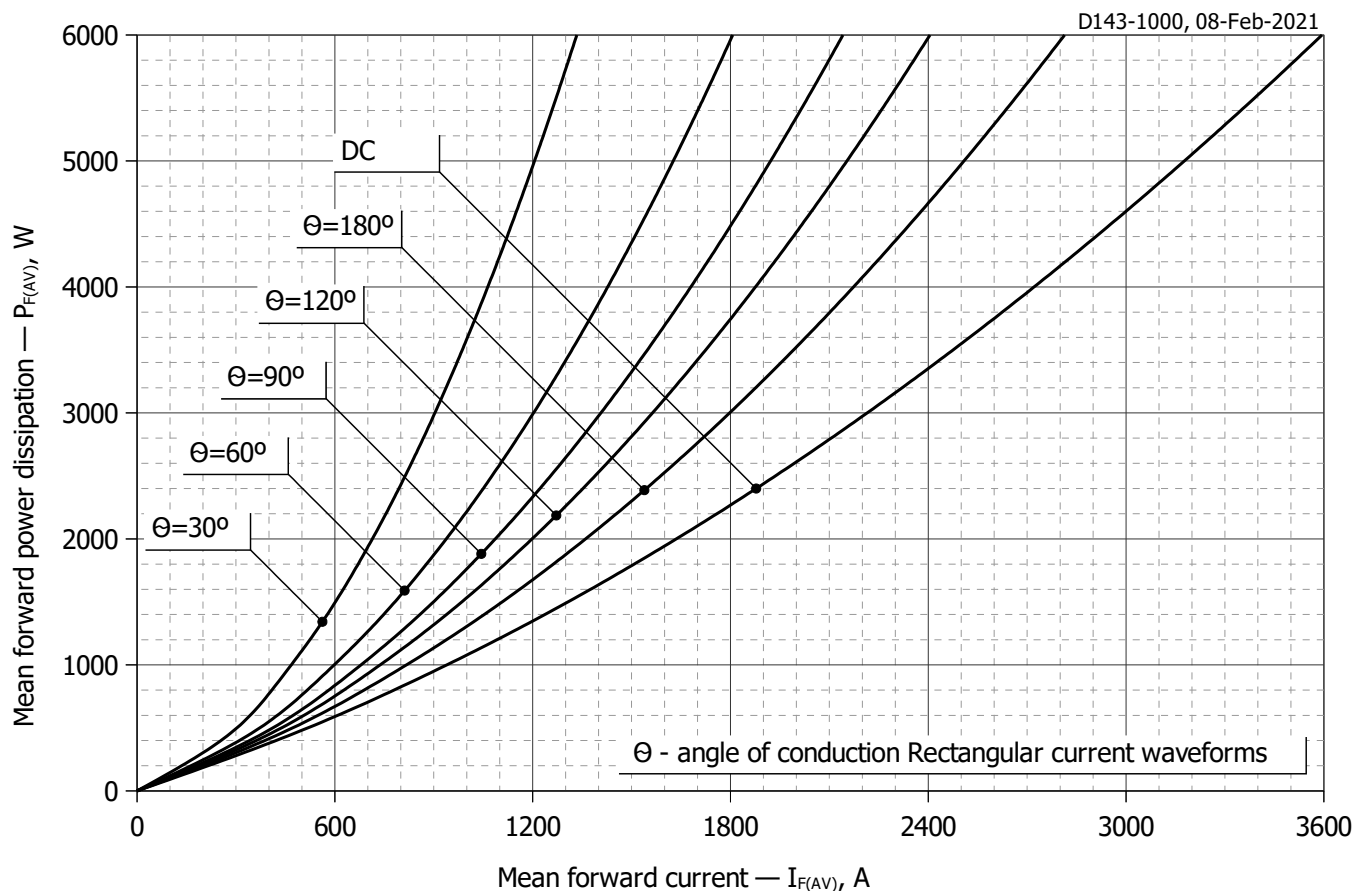


Fig. 8 – Mean forward power dissipation P_{FAV} vs. mean forward current I_{FAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

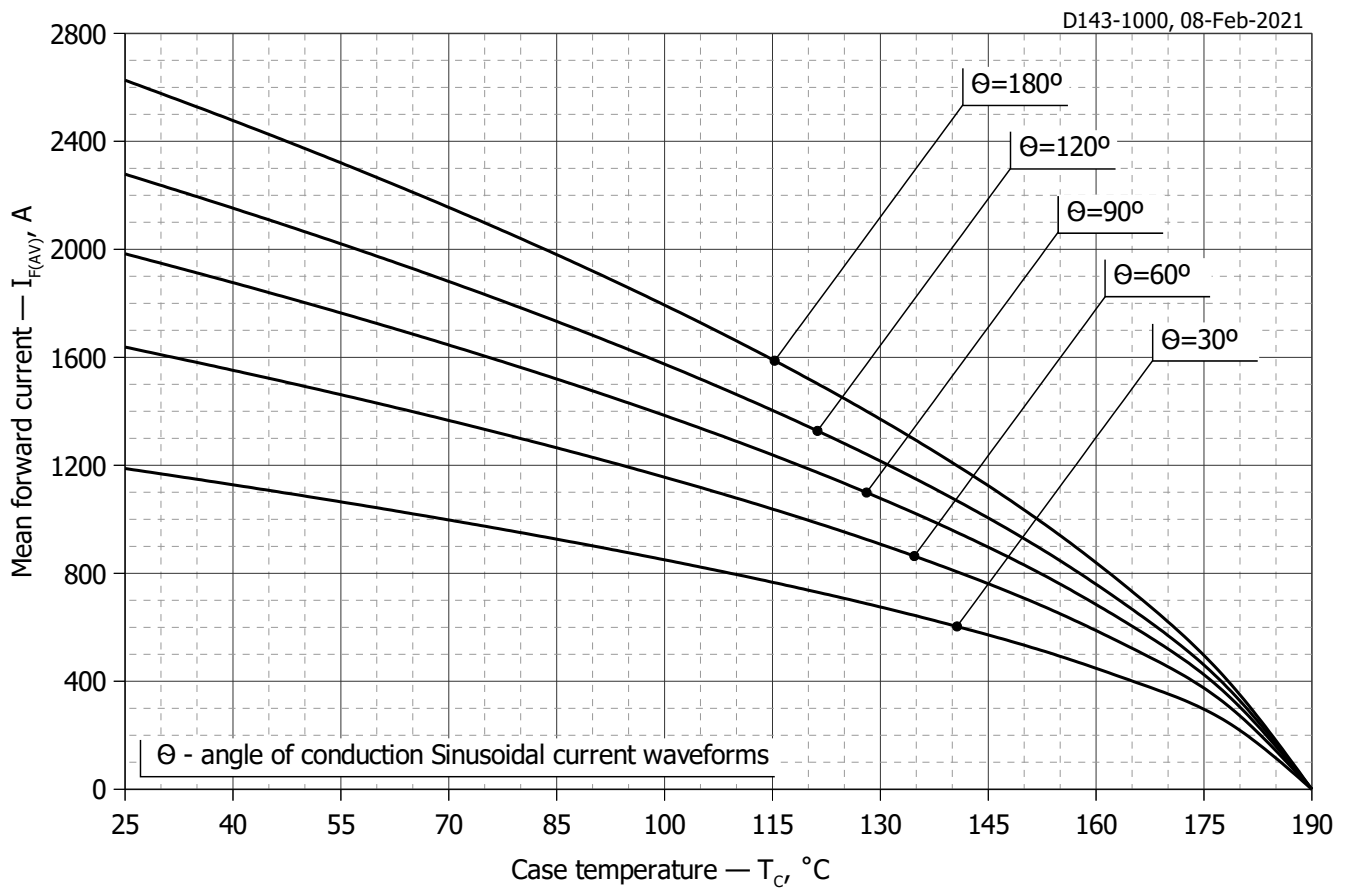


Fig. 9 – Mean forward current I_{FAV} vs. case temperature T_C for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

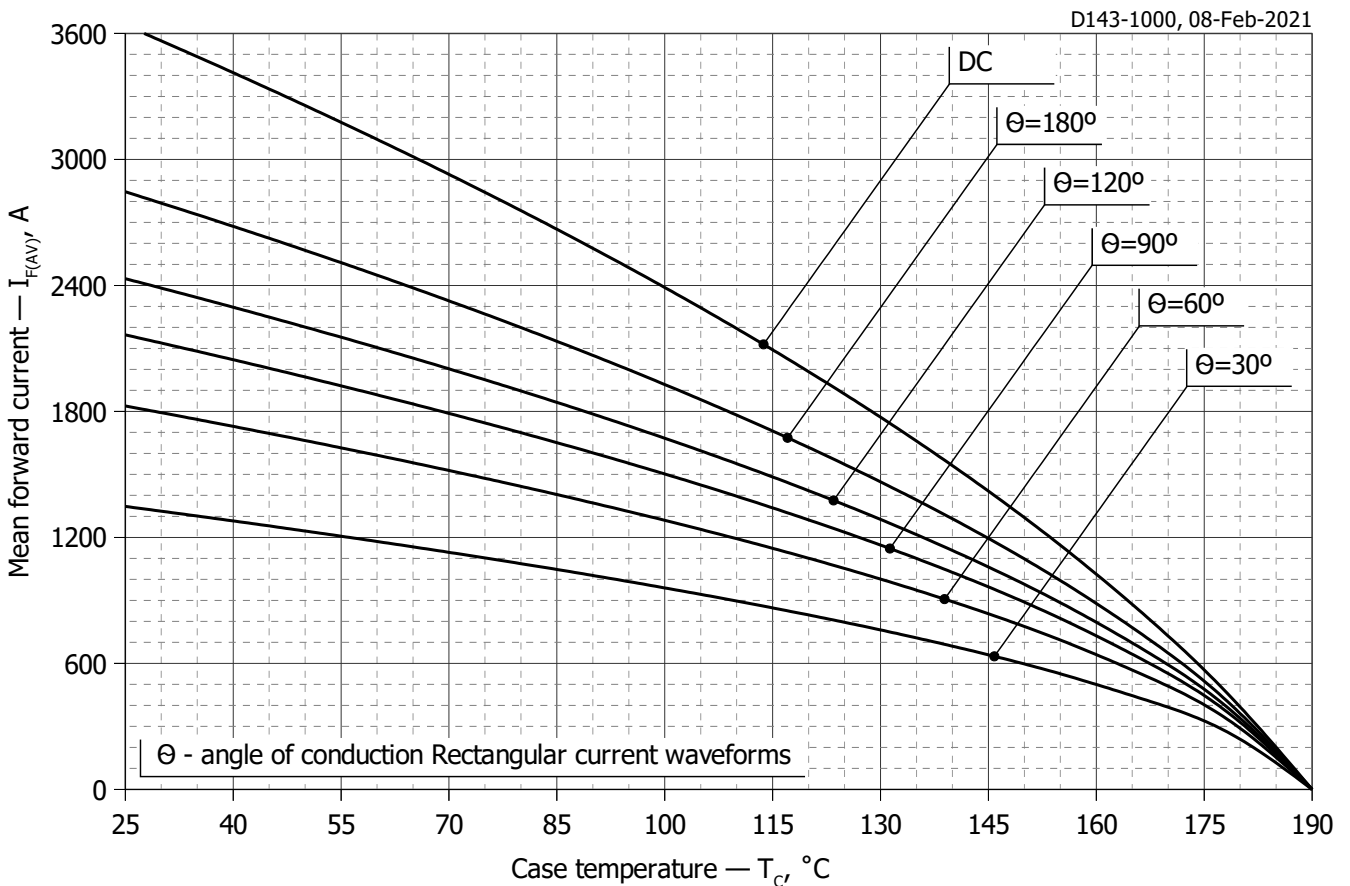


Fig. 10 - Mean forward current I_{FAV} vs. case temperature T_C for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

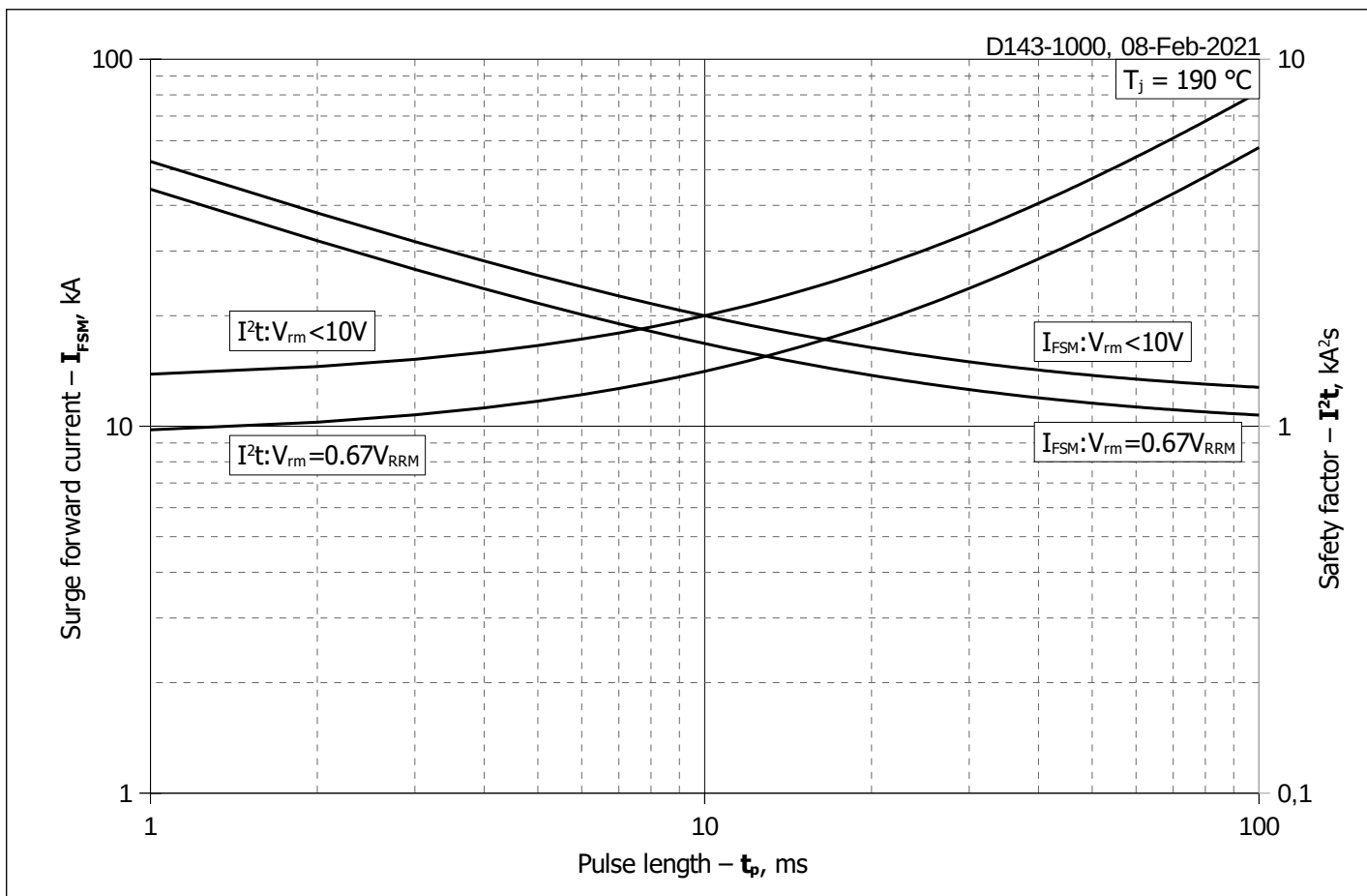


Fig. 11 – Maximum surge forward current I_{FSM} and safety factor I^2t vs. pulse length t_p

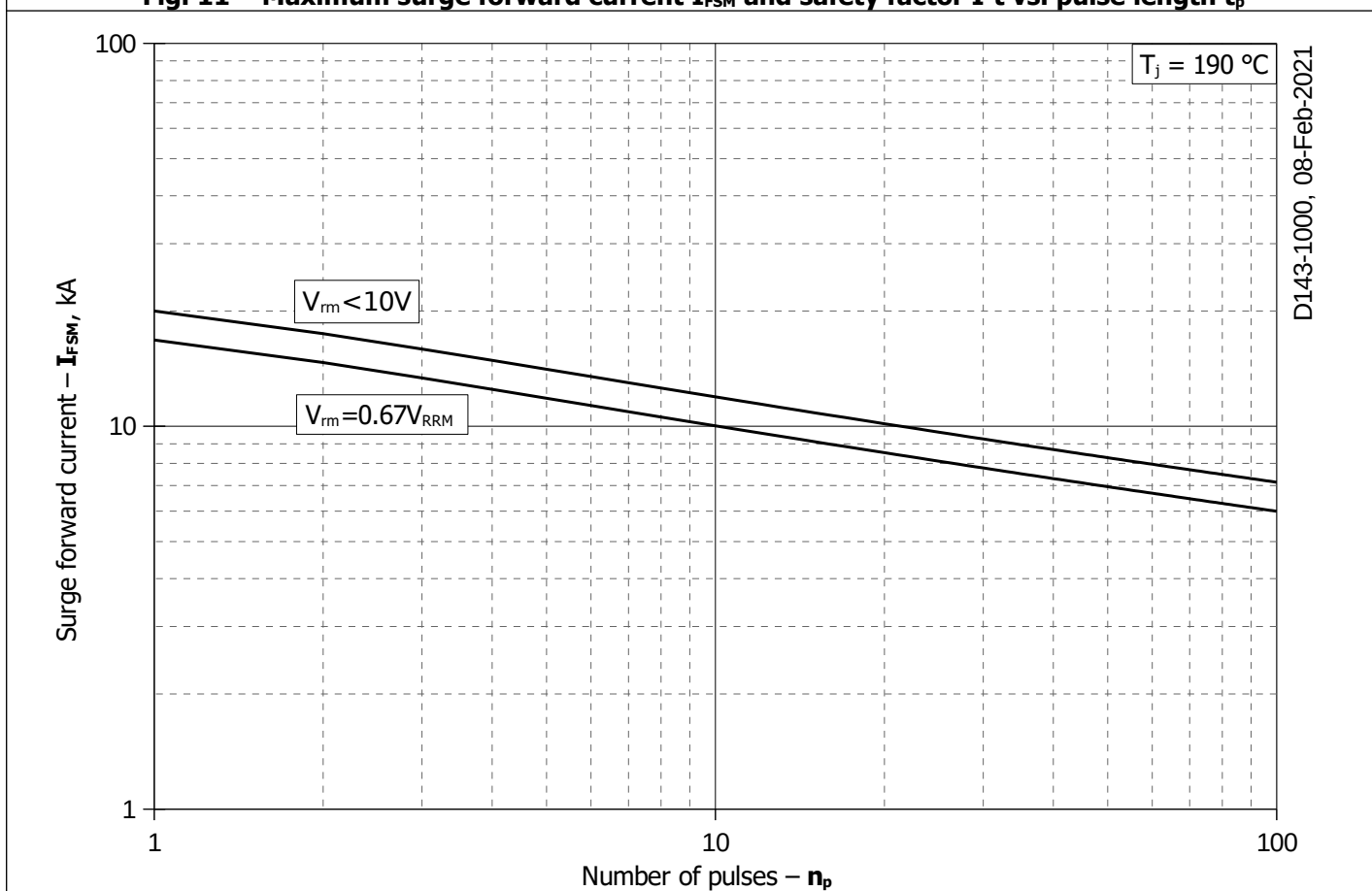


Fig. 12 - Maximum surge forward current I_{FSM} vs. number of pulses n_p